

N-Channel Power MOSFET

600V, 8A, 0.6Ω

FEATURES

- Super-Junction technology
- High performance due to small figure-of-merit
- High ruggedness performance
- High commutation performance

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- Power Supply
- Lighting

KEY PERFORMANCE PARAMETERS				
PARAMETER VALUE UNIT				
V_{DS}	600	V		
R _{DS(on)} (max)	0.6	Ω		
Q_g	13	nC		



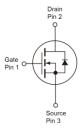












Notes: MSL 3 (Moisture Sensitivity Level) for TO-252 (D-PAK) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	ITO-220	IPAK/DPAK	UNIT
Drain-Source Voltage		V _{DS}	600		V
Gate-Source Voltage		V_{GS}	±30		V
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$		8 4.8		A
Continuous Drain Current	T _C = 100°C	l _D			
Pulsed Drain Current (Note 2)		I _{DM}	24		Α
Total Power Dissipation @ T _C = 25°C		P _{DTOT}	32	83	W
Single Pulsed Avalanche Energy (Note 3)		E _{AS}	100		mJ
Single Pulsed Avalanche Current (Note 3)		I _{AS}	2		Α
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150		°C

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	ITO-220	IPAK/DPAK	UNIT
Junction to Case Thermal Resistance	R _{eJC}	3.9 1.5		°C/W
Junction to Ambient Thermal Resistance	R _{OJA}	62		°C/W

Notes: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. $R_{\theta JA}$ shown below for single device operation on FR-4 PCB in still air.





ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	600			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	2.0	3.0	4.0	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	I _{DSS}			1	μΑ
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 4A$	R _{DS(on)}		0.49	0.6	Ω
Dynamic (Note 5)						
Total Gate Charge	.,	Qg		13		
Gate-Source Charge	$V_{DS} = 380V, I_{D} = 8A,$	Q_{gs}		3		nC
Gate-Drain Charge	$V_{GS} = 10V$	Q_{gd}		4		1
Input Capacitance	$V_{DS} = 100V, V_{GS} = 0V,$	C _{iss}		743		. –
Output Capacitance	f = 1.0MHz	C _{oss}		66		pF
Gate Resistance	F = 1MHz, open drain	R_g		3.2		Ω
Switching (Note 6)						
Turn-On Delay Time		t _{d(on)}		21		
Turn-On Rise Time	$V_{DD} = 380V$,	t _r		15		
Turn-Off Delay Time	$R_{GEN} = 25\Omega,$ $I_D = 8A, V_{GS} = 10V,$	t _{d(off)}		40		ns
Turn-Off Fall Time	$I_D = OA$, $V_{GS} = TOV$,	t _f		9]
Source-Drain Diode (Note 4)		•				
Forward On Voltage	I _S = 8A, V _{GS} = 0V	V _{SD}			1.4	V
Reverse Recovery Time	V _R =200V, I _S = 4A	t _{rr}		185		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Q _{rr}		1.4		μC

Notes:

- 1. Current limited by package
- 2. Pulse width limited by the maximum junction temperature
- 3. L = 50mH, $I_{AS} = 2A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25^{\circ}C$
- 4. Pulse test: PW \leq 300 μ s, duty cycle \leq 2%
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.





ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM60N600CI COG	ITO-220	50pcs / Tube
TSM60N600CH C5G	TO-251 (IPAK)	75pcs / Tube
TSM60N600CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel

Note:

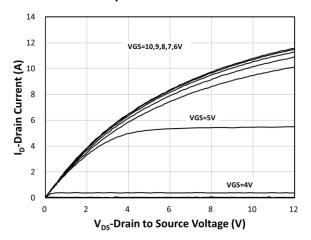
- 1. Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- 2. Halogen-free according to IEC 61249-2-21 definition



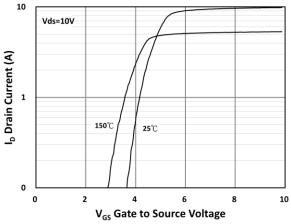
ELECTRICAL CHARACTERISTICS CURVES

(T_C = 25°C unless otherwise noted)

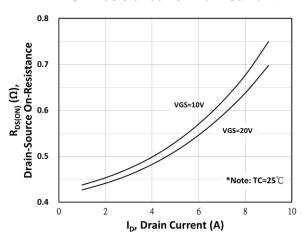
Output Characteristics



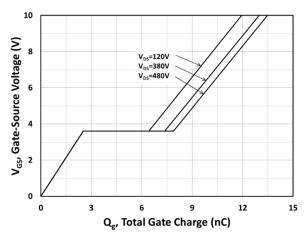
Transfer Characteristics



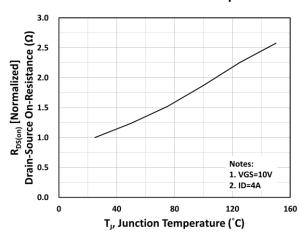
On-Resistance vs. Drain Current



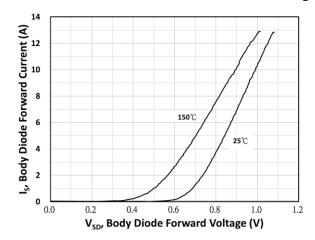
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Current vs. Voltage

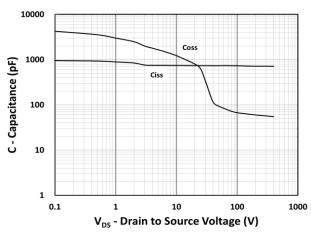




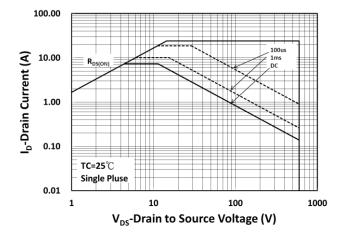
ELECTRICAL CHARACTERISTICS CURVES

(T_C = 25°C unless otherwise noted)

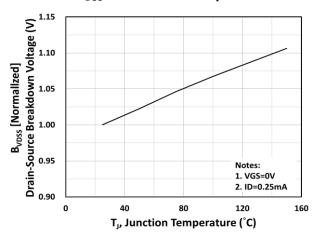
Capacitance vs. Drain-Source Voltage



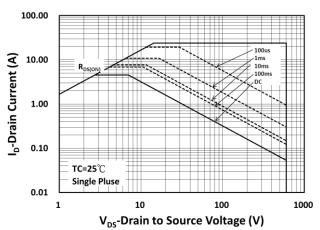
Maximum Safe Operating Area (DPAK/IPAK)



BV_{DSS} vs. Junction Temperature



Maximum Safe Operating Area (ITO-220)

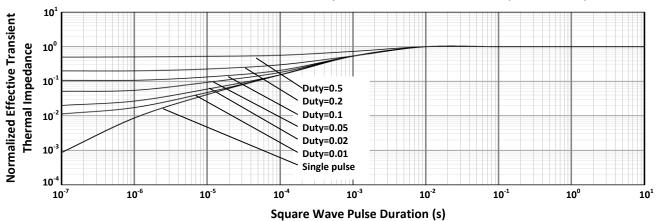




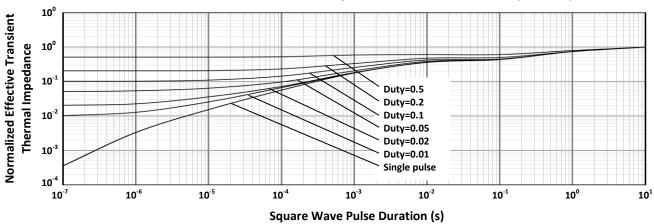
ELECTRICAL CHARACTERISTICS CURVES

 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$

Normalized Thermal Transient Impedance, Junction-to-Case (DPAK/IPAK)

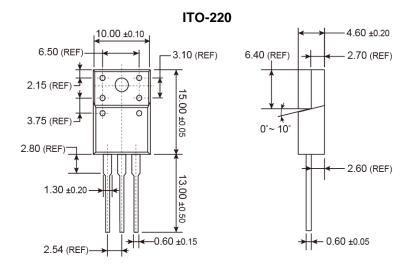


Normalized Thermal Transient Impedance, Junction-to-Case (ITO-220)





PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



MARKING DIAGRAM



3 = Halogen Free

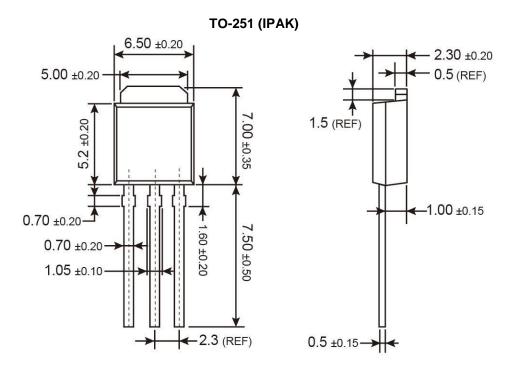
Y = Year Code

WW = Week Code (01~52)

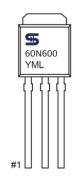
F = Factory Code



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

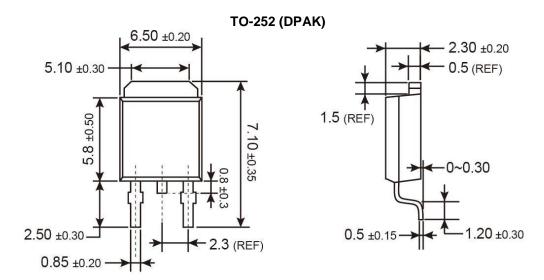
 $oldsymbol{O}$ =Jan $oldsymbol{P}$ =Feb $oldsymbol{Q}$ =Mar $oldsymbol{R}$ =Apr

S =May T =Jun U =Jul V =Aug W =Sep X =Oct Y =Nov Z =Dec

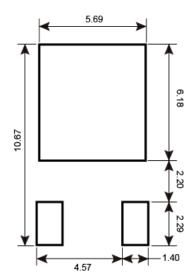
W =Sep **X** =Oct **Y** =Nov **Z L** = Lot Code (1~9, A~Z)



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



SUGGESTED PAD LAYOUT



MARKING DIAGRAM



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S = May T = Jun U = Jul V = Aug

W = Sep X = Oct Y = Nov Z = Dec

 $\mathbf{L} = \text{Lot Code } (1 \sim 9, A \sim Z)$





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